Power MOSFET

100 V, 12 A, N–Channel, Logic Level DPAK

Features

- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Avalanche Energy Specified
- Logic Level
- Pb–Free Packages are Available

Typical Applications

- PWM Motor Controls
- Power Supplies
- Converters

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

(1) = 25 of unless otherwise noted)			
Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	100	Vdc
Drain-to-Source Voltage (R_{GS} = 1.0 M Ω)	V _{DGR}	100	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	± 20	Vdc
Drain Current – Continuous @ T _A = 25°C – Continuous @ T _A =100°C – Pulsed (Note 3)	I _D I _D I _{DM}	12 9.0 44	Adc Apk
Total Power Dissipation Derate above 25°C Total Power Dissipation @ $T_A = 25°C$ (Note 1) Total Power Dissipation @ $T_A = 25°C$ (Note 2)	P _D	56.6 0.38 1.76 1.28	W W/°C W W
Operating and Storage Temperature Range	T _J , T _{stg}	–55 to +175	°C
$ \begin{array}{l} \mbox{Single Pulse Drain-to-Source Avalanche} \\ \mbox{Energy} - \mbox{Starting } T_J = 25^\circ \mbox{C} \\ \mbox{(V}_{DD} = 50 \mbox{ Vdc}, \mbox{V}_{GS} = 5.0 \mbox{ Vdc}, \\ \mbox{I}_L = 12 \mbox{ Apk}, \mbox{L} = 1.0 \mbox{ mH}, \mbox{R}_G = 25 \Omega \mbox{)} \end{array} $	E _{AS}	72	mJ
Thermal Resistance – Junction-to-Case – Junction-to-Ambient (Note 1) – Junction-to-Ambient (Note 2)	R _θ jc R _θ ja R _θ ja	2.65 85 117	°C/W
Maximum Temperature for Soldering Purposes, (1/8" from case for 10 s)	ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

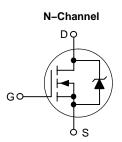
- 1. When surface mounted to an FR4 board using 0.5 sq in pad size.
- 2. When surface mounted to an FR4 board using the minimum recommended pad size.
- 3. Pulse Test: Pulse Width = 10 μ s, Duty Cycle = 2%.

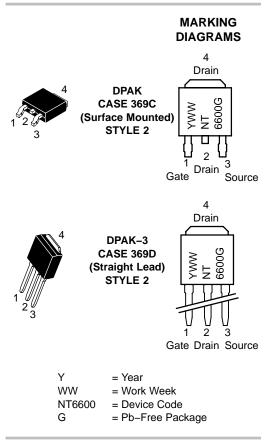


ON Semiconductor®

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V _{(BR)DSS} R _{DS(on)} TYP		I _D MAX
100 V	118 mΩ @ 5.0 V	12 A





ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

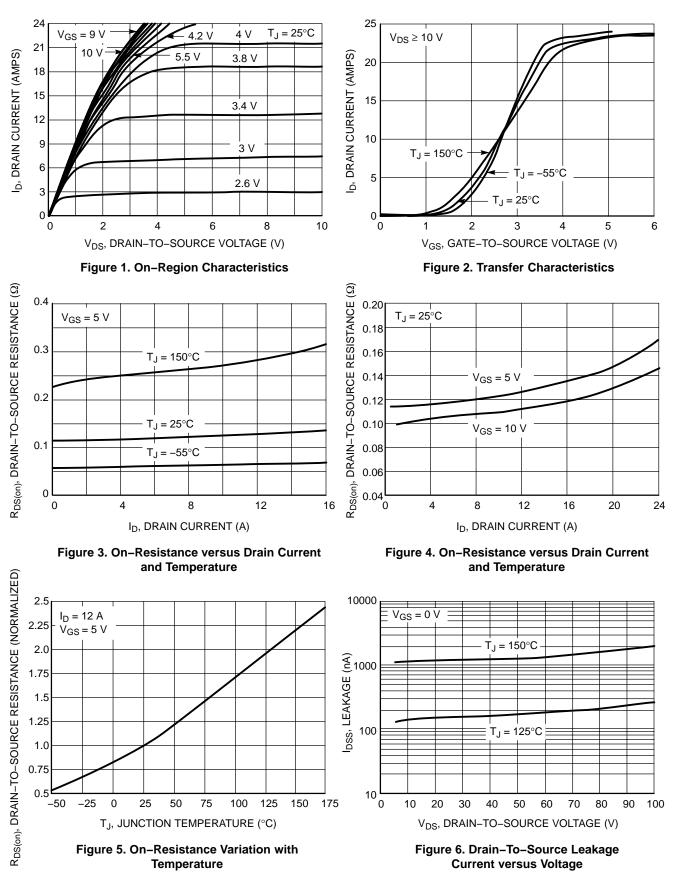
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		-	-	-	-	-
Drain-to-Source Breakdown Volta $(V_{GS} = 0 \text{ Vdc}, I_D = 250 \mu \text{Adc})$	V _{(BR)DSS}	100	_	_	Vdc	
Zero Gate Voltage Drain Current ($V_{GS} = 0 \text{ Vdc}, V_{DS} = 100 \text{ Vdc}, T_J = 25^{\circ}\text{C}$) ($V_{GS} = 0 \text{ Vdc}, V_{DS} = 100 \text{ Vdc}, T_J = 125^{\circ}\text{C}$)		I _{DSS}			1.0 10	μAdc
Gate-Body Leakage Current (VGS	= ± 20 Vdc, V _{DS} = 0)	I _{GSS}	-	-	±100	nAdc
ON CHARACTERISTICS		•			•	•
Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \ \mu Adc$) Temperature Coefficient (Nega	tive)	V _{GS(th)}	1.0 _	1.5 -4.4	2.0	Vdc mV/°C
Static Drain-to-Source On-State	Resistance (V_{GS} = 5.0 Vdc, I_D = 6.0 Adc)	R _{DS(on)}	-	118	146	mΩ
Drain-to-Source On-Voltage (VGS	_S = 5.0 Vdc, I _D = 12 Adc)	V _{DS(on)}	-	1.5	2.2	Vdc
Forward Transconductance (V _{DS} =	= 10 Vdc, I _D = 6.0 Adc)	9fs	-	10	-	mhos
DYNAMIC CHARACTERISTICS		•			•	•
Input Capacitance		C _{iss}	-	463	700	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C _{oss}	-	116	225	
Reverse Transfer Capacitance	· · · · · · · · · · · · · · · · · · ·	C _{rss}	-	36	75	
SWITCHING CHARACTERISTICS	(Notes 4 & 5)					
Turn-On Delay Time		t _{d(on)}	-	10.5	20	ns
Rise Time	(V _{DD} = 80 Vdc, I _D = 6.0 Adc,	tr	-	75	140	
Turn-Off Delay Time	$V_{GS} = 5.0 \text{ Vdc}, \text{ R}_{G} = 9.1 \Omega$	t _{d(off)}	-	26	40	
Fall Time		t _f	-	50	90	
Total Gate Charge		Q _{tot}	-	11.3	20	nC
Gate-to-Source Charge	$(V_{DS} = 80 \text{ Vdc}, I_D = 6.0 \text{ Adc}, V_{GS} = 5.0 \text{ Vdc})$	Q _{gs}	-	1.9	-	
Gate-to-Drain Charge		Q _{gd}	-	7.4	-	
BODY-DRAIN DIODE RATINGS (M	Note 4)					
Diode Forward On–Voltage	$(I_{S} = 12 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$ $(I_{S} = 12 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_{J} = 125^{\circ}\text{C})$	V _{SD}		0.90 0.80	1.4 -	Vdc
Reverse Recovery Time		t _{rr}	-	80	-	ns
	(I _S = 12 Adc, V _{GS} = 0 Vdc, dI _S /dt = 100 A/μs)	t _a	-	50	-	
		t _b	-	30	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.240	-	μC

Indicates Pulse Test: P.W. = 300 μs max, Duty Cycle = 2%.
Switching characteristics are independent of operating junction temperature.

ORDERING INFORMATION

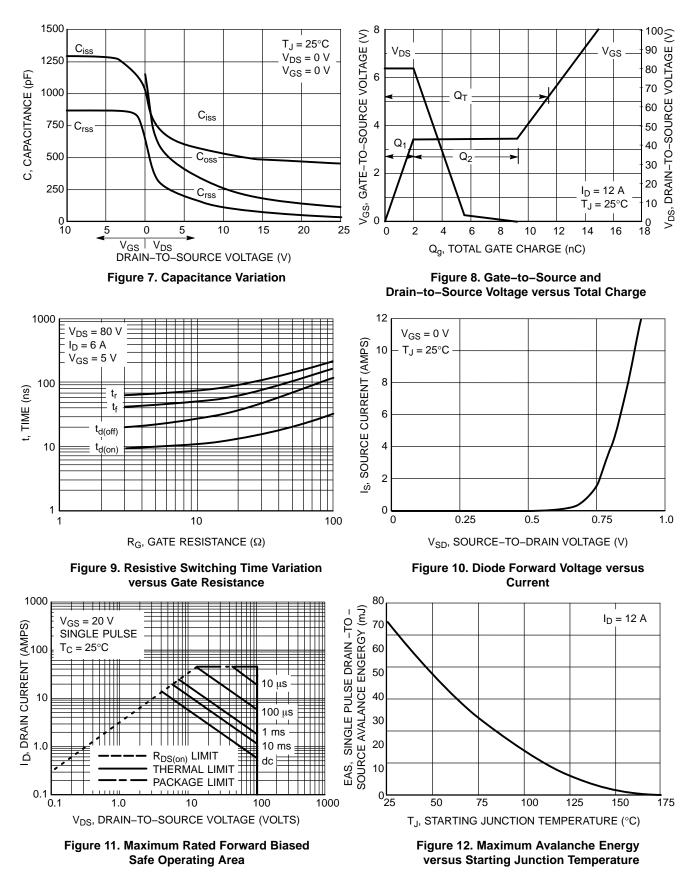
Device	Package	Shipping [†]	
NTD6600N	DPAK		
NTD6600N-1	DPAK-3	75 Units/Rail	
NTD6600N-1G	DPAK-3 (Pb-Free)	- 75 Units/Rail	
NTD6600NT4	DPAK		
NTD6600NT4G	DPAK (Pb–Free)	2500 Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



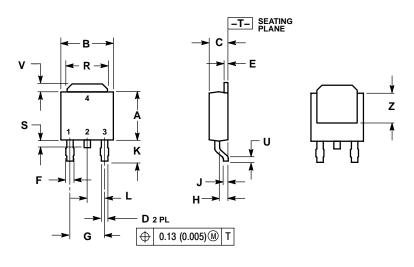
TYPICAL CHARACTERISTICS

TYPICAL CHARACTERISTICS



PACKAGE DIMENSIONS

DPAK CASE 369C-01 ISSUE O

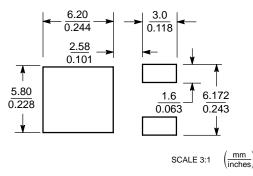


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
в	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.180	BSC	4.58 BSC		
н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
ĸ	0.102	0.114	2.60	2.89	
L	0.090	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
٧	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

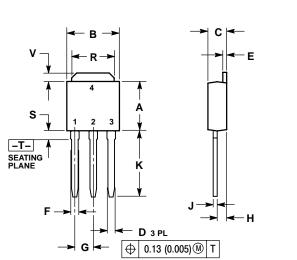
STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

SOLDERING FOOTPRINT*

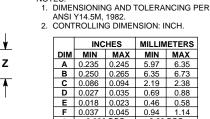


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



DPAK-3 CASE 369D-01 ISSUE B



NOTES

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.090 BSC		2.29	BSC	
н	0.034	0.040	0.87 1.0		
J	0.018	0.023	0.46	0.58	
κ	0.350	0.380	8.89	9.65	
R	0.180	0.215	4.45	5.45	
S	0.025	0.040	0.63	1.01	
V	0.035	0.050	0.89	1.27	
Ζ	0.155		3.93		

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE DRAIN 4

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